

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Divisional Patent Application of)
Shunpei YAMAZAKI et al.)
Based On Application No. 10/084,428) Attn: Applications
Filed: February 28, 2002) Branch
For: SEMICONDUCTOR DEVICE HAVING)
SEMICONDUCTOR CIRCUIT FORMED BY)
SEMICONDUCTOR ELEMENTS AND METHOD)
FOR MANUFACTURING THE SAME) Date: March 31, 2004

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. §1.56, Applicants hereby submit the following information in conformance with 37 C.F.R. §§ 1.97 and 1.98. Pursuant to 37 C.F.R. § 1.98, a copy of each of the documents cited is enclosed.

The references listed on the attached Form PTO-1449 were cited in parent application Serial No. 10/084,428 filed February 28, 2002, from which priority is claimed under 35 U.S.C. 120.

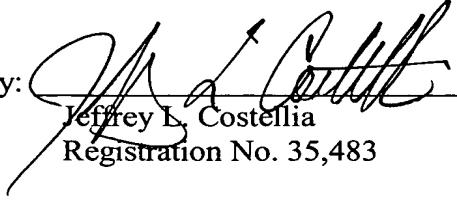
It is requested that the accompanying PTO-1449 be considered and made of record in the above-identified application. To assist the Examiner, the documents are listed on the attached form PTO-1449. It is respectfully requested that an Examiner initialed copy of this form be returned to the undersigned.

Docket No: 740756-2719

The Commissioner is hereby authorized to charge any fees connected with this filing which may be required now, or credit any overpayment to Deposit Account No. 19-2380.

Respectfully submitted,

By:


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Substitute for form 1449A/PTO				<i>Complete if Known</i>	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	New Application
Sheet	1	of	1	Filing Date	March 31, 2004
				First Named Inventor	Shunpei YAMAZAKI et al.
				Art Unit	2826
				Examiner Name	S. Wilson
				Attorney Docket Number	740756-2719

U.S. PATENT DOCUMENTS					
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
		US-5,861,656	01/19/1999	Keri	
		US-5,471,330	11/28/1995	Sarma	
		US-6,147,667	11/14/2000	Yamazaki et al	
		US-5,767,531	06/16/1998	Yoshinouchi	
		US-6,246,070	06/12/2001	Yamazaki et al	
		US-5,763,301	06/09/1998	Rha et al	
		US-5,818,067	10/06/1998	Rha et al	
		US-6,147,667	11/14/2000	Yamazaki et al.	
		US-5,403,762	04/04/1995	Takemura	
		US-5,342,545	08/30/1994	Yamada et al.	
		US-5,471,330	11/28/1995	Sarma	

FOREIGN PATENT DOCUMENTS					
Examiner Initials ¹	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Kind Code ³ Country Code ³ Number ⁴ (if known)			
		JP 07-142734-A	06/02/1995		Abstract
		JP 58-163722-A	09/28/1983	Yabuki et al	Abstract
		JP 61-070780-A	04/11/1986	Oda et al	Abstract

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS					
Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²
		Lim et al. "High Performance Amorphous Silicon Thin Film Transistor with a Planarized SIN _x /BCB Double-Layered Gate Insulator", AM-LCD '98 pp. 73-76			
		Won et al. "28.3: A High-Resolution Full Color TFT-LCD on Transparent Plastic", SID 03 DIGEST, pp. 992-995			
		Jang et al. "32.1: Invited Paper: Amorphous Silicon Thin-Film Transistors with Planarized Gate Insulators" (4 pages)			
		Wolf, Silicon Processing for the VLSI Era, 1990, Lattice Press, Volume 2, p. 273-274, 354, 356-357, 359.			

Examiner Signature	Date Considered
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached